

20 V, 4.3 A NPN low VCEsat transistor

7 February 2024

Product data sheet

1. General description

NPN low V_{CEsat} transistor in a SOT23 small Surface-Mounted Device (SMD) plastic package.

PNP complement: PBSS4021PT

2. Features and benefits

- Very low collector-emitter saturation voltage V_{CEsat}
- High collector current capability I_C and I_{CM}
- High collector current gain (h_{FE}) at high I_C
- · High energy efficiency due to less heat generation
- Smaller required Printed-Circuit Board (PCB) area than for conventional transistors
- AEC-Q101 qualified

3. Applications

- Loadswitch
- Battery-driven devices
- Power management
- Charging circuits
- Power switches (e.g. motors, fans)

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{CEO}	collector-emitter voltage	open base	-	-	20	V
I _C	collector current		-	-	4.3	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms	-	-	8	Α
R _{CEsat}	collector-emitter saturation resistance	I_C = 4 A; I_B = 400 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	36	55	mΩ



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base	3	С
2	Е	emitter		j
3	С	collector		В — (
				 E
			SOT23	sym021

6. Ordering information

Table 3. Ordering information

Type number	Package	Package				
	Name	Description	Version			
PBSS4021NT	SOT23	plastic, surface-mounted package; 3 terminals; 1.9 mm pitch; 2.9 mm x 1.3 mm x 1 mm body	SOT23			

7. Marking

Table 4. Marking codes

Type number	Marking code[1]
PBSS4021NT	%BH

[1] % = placeholder for manufacturing site code

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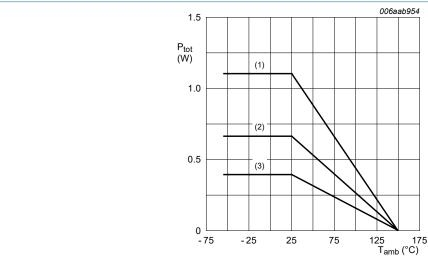
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter		-	20	V
V_{CEO}	collector-emitter voltage	open base		-	20	V
V _{EBO}	emitter-base voltage	open collector		-	5	V
I _C	collector current			-	4.3	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	8	А
I _B	base current			-	1	А
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	390	mW
			[2]	-	660	mW
			[3]	-	1100	mW
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².
- [3] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.



- (1) Ceramic PCB, Al₂O₃, standard footprint
- (2) FR4 PCB, mounting pad for collector 1 cm²
- (3) FR4 PCB, standard footprint

Fig. 1. Power derating curves

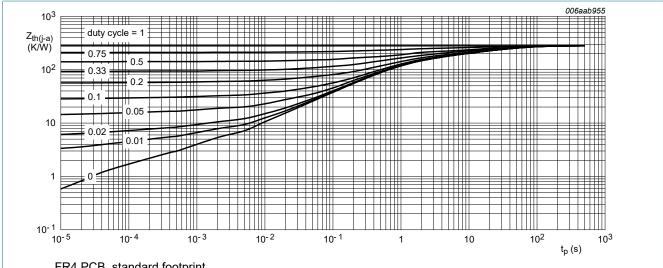
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9. Thermal characteristics

Table 6. Thermal characteristics

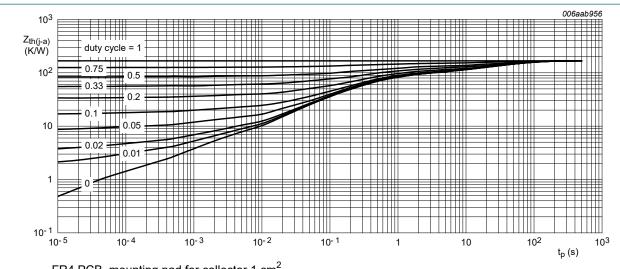
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
· ·ui(j-a)	thermal resistance from		[1]	-	-	320	K/W
	junction to ambient		[2]	-	-	190	K/W
			[3]	-	-	115	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	-	62	K/W

- Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².
- Device mounted on a ceramic PCB, Al₂O₃, standard footprint.



FR4 PCB, standard footprint

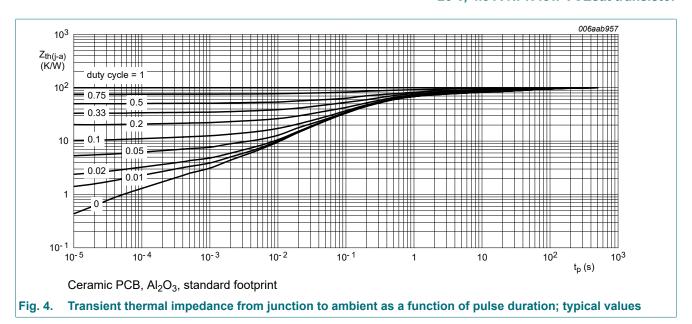
Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for collector 1 cm²

Transient thermal impedance from junction to ambient as a function of pulse duration; typical values Fig. 3.

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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off	V _{CB} = 20 V; I _E = 0 A; T _{amb} = 25 °C	-	-	100	nA
	current	$V_{CB} = 20 \text{ V}; I_E = 0 \text{ A}; T_j = 150 ^{\circ}\text{C}$	-	-	50	μΑ
I _{EBO}	emitter-base cut-off current	V _{EB} = 5 V; I _C = 0 A; T _{amb} = 25 °C	-	-	100	nA
I _{CES}	collector-emitter cut-off current	V _{CE} = 16 V; V _{BE} = 0 V; T _{amb} = 25 °C	-	-	100	nA
h _{FE}	DC current gain	V _{CE} = 2 V; I _C = 500 mA; T _{amb} = 25 °C	300	550	-	
		V_{CE} = 2 V; I_{C} = 1 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	300	500	-	
		V_{CE} = 2 V; I_{C} = 2 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	300	420	-	
		V_{CE} = 2 V; I_{C} = 4 A; pulsed; $t_{p} \le 300 \ \mu s$; δ ≤ 0.02; T_{amb} = 25 °C	150	260	-	
		V_{CE} = 2 V; I_{C} = 6 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	100	170	-	
V _{CEsat}	collector-emitter saturation voltage	I_C = 1 A; I_B = 50 mA; pulsed; t_p ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	42	60	mV
		I_C = 1 A; I_B = 10 mA; pulsed; t_p ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	55	75	mV
		I_C = 2 A; I_B = 40 mA; pulsed; $t_p \le$ 300 µs; $\delta \le 0.02$; T_{amb} = 25 °C	-	85	120	mV
		I_C = 4 A; I_B = 200 mA; pulsed; $t_p \le$ 300 µs; $\delta \le$ 0.02; T_{amb} = 25 °C	-	155	220	mV
		I_C = 4 A; I_B = 40 mA; pulsed; $t_p \le$ 300 µs; $\delta \le 0.02$; T_{amb} = 25 °C	-	190	265	mV
		$I_C = 4 \text{ A}$; $I_B = 400 \text{ mA}$; pulsed; $t_p \le$	-	145	200	mV
R _{CEsat}	collector-emitter saturation resistance	300 μs; δ ≤ 0.02; T _{amb} = 25 °C	-	36	55	mΩ
V _{BEsat}	base-emitter saturation voltage	I_C = 1 A; I_B = 100 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	0.94	1.05	V
		I_C = 4 A; I_B = 400 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	1.17	1.25	V
V_{BEon}	base-emitter turn-on voltage	V_{CE} = 2 V; I_{C} = 2 A; pulsed; $t_{p} \le 300 \ \mu s$; δ ≤ 0.02; T_{amb} = 25 °C	-	0.81	0.9	V
t _d	delay time	$V_{CC} = 12.5 \text{ V}; I_C = 1 \text{ A}; I_{Bon} = 0.05 \text{ A};$	-	15	-	ns
t _r	rise time	I _{Boff} = -0.05 A; T _{amb} = 25 °C	-	45	-	ns
t _{on}	turn-on time		-	60	-	ns
t _s	storage time		-	490	-	ns
t _f	fall time		-	80	-	ns
t _{off}	turn-off time		-	570	-	ns
f⊤	transition frequency	V_{CE} = 10 V; I_{C} = 100 mA; f = 100 MHz; T_{amb} = 25 °C	-	165	-	MHz
C _c	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = 0 \text{ A}; i_e = 0 \text{ A}; f = 1 \text{ MHz}; $ $T_{amb} = 25 ^{\circ}\text{C}$	-	36	-	pF

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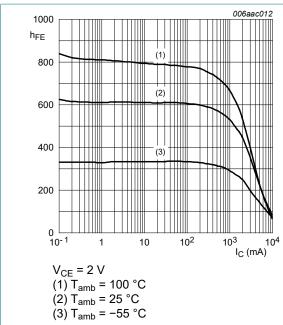
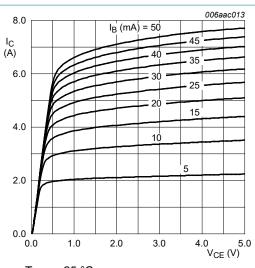
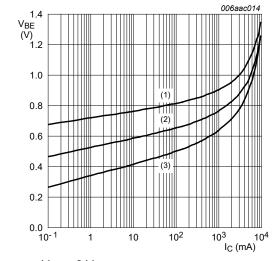


Fig. 5. DC current gain as a function of collector current; typical values



 T_{amb} = 25 °C

Fig. 6. Collector current as a function of collectoremitter voltage; typical values



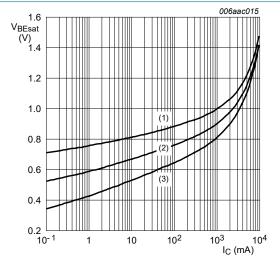
 $V_{CE} = 2 V$

(1) $T_{amb} = -55$ °C

(2) $T_{amb} = 25 \, ^{\circ}C$

(3) $T_{amb} = 100 \, ^{\circ}C$

Fig. 7. Base-emitter voltage as a function of collector current; typical values



 $I_C/I_B = 20$

(1) $T_{amb} = -55$ °C

(2) $T_{amb} = 25 \, ^{\circ}C$

(3) $T_{amb} = 100 \, ^{\circ}C$

Fig. 8. Base-emitter saturation voltage as a function of collector current; typical values

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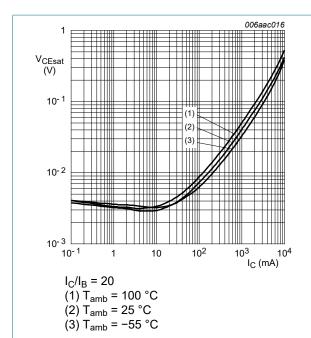


Fig. 9. Collector-emitter saturation voltage as a function of collector current; typical values

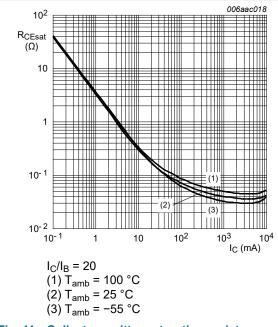


Fig. 11. Collector-emitter saturation resistance as a function of collector current; typical values

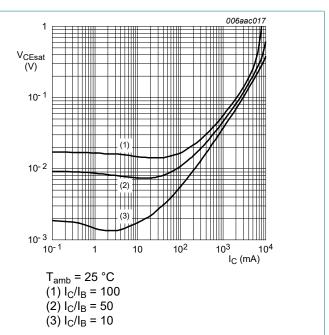


Fig. 10. Collector-emitter saturation voltage as a function of collector current; typical values

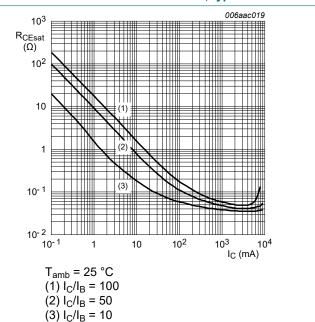
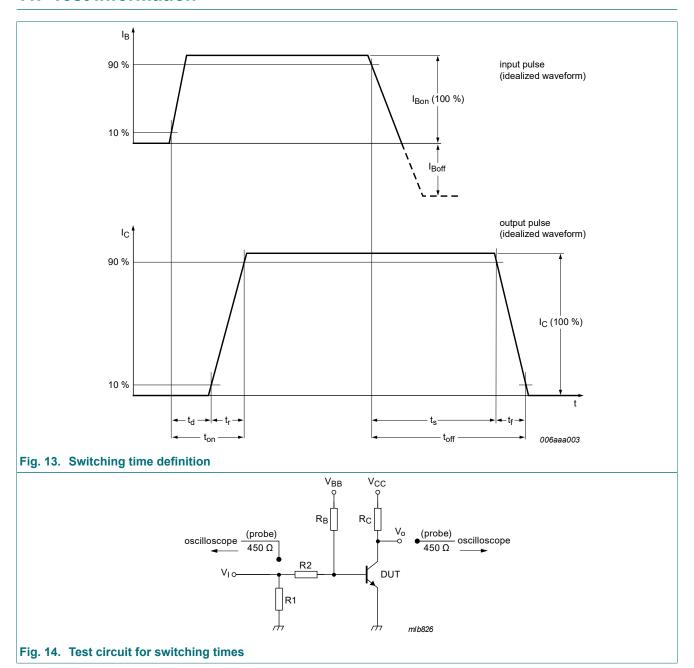


Fig. 12. Collector-emitter saturation resistance as a function of collector current; typical values

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11. Test information

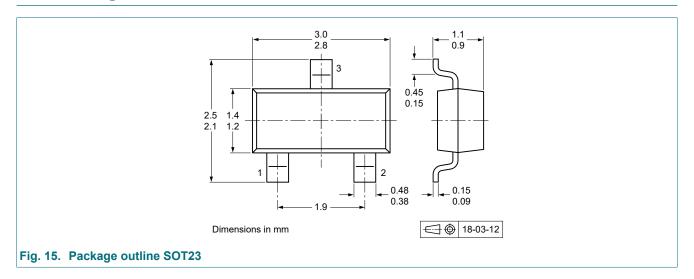


Quality information

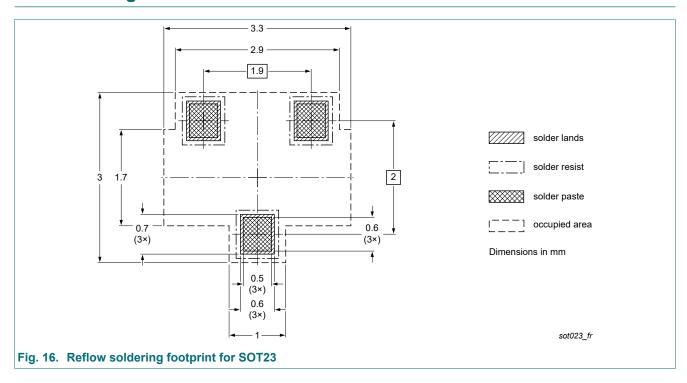
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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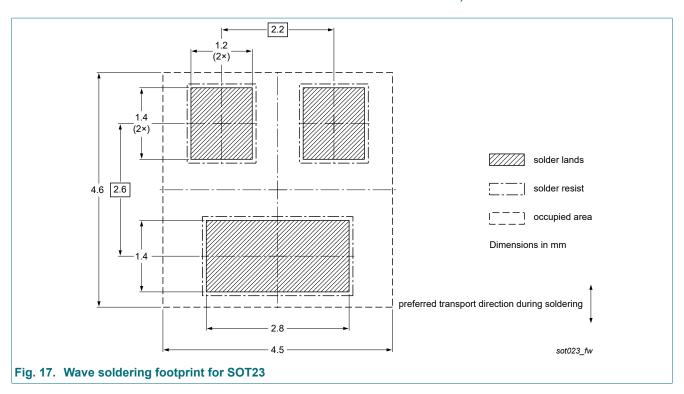
12. Package outline



13. Soldering



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14. Revision history

Table 8. Revision history

Table of Iteriological	J. U. J							
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes				
PBSS4021NT v.2	20240207	Product data sheet	-	PBSS4021NT v.1				
Modifications:	Nexperia. • Legal texts ha	 The format of this data sheet has been redesigned to comply with the identity guidelines of Nexperia. Legal texts have been adapted to the new company name where appropriate. Section "Packing information" removed. 						
PBSS4021NT v.1	20100131	Product data sheet	-	-				

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15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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PBSS4021NT

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